

N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product data of

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see Figure 12; see Figure 13		-	5.98	7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>		-	3.74	4.4	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 25 A; V_{DS} = 30 V;		-	14.8	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	70.8	-	nC
	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω; unclamped		-	-	266	mJ

[1] Continuous current is limited by package.

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N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information Type number Package Name Description Version PSMN4R6-60BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R6-60BS	PSMN4R6-60BS

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		57 (7				
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	99.7	А
		T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; t _p = 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	565	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	211	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p = 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	565	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} \leq 60 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} \end{array} $		-	266	mJ

[1] Continuous current is limited by package.

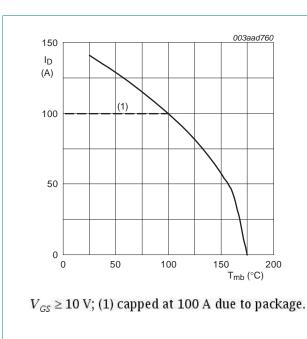
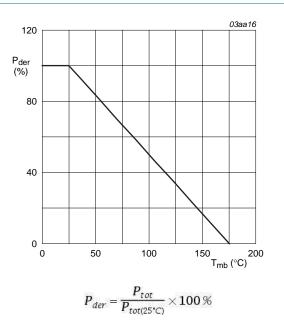
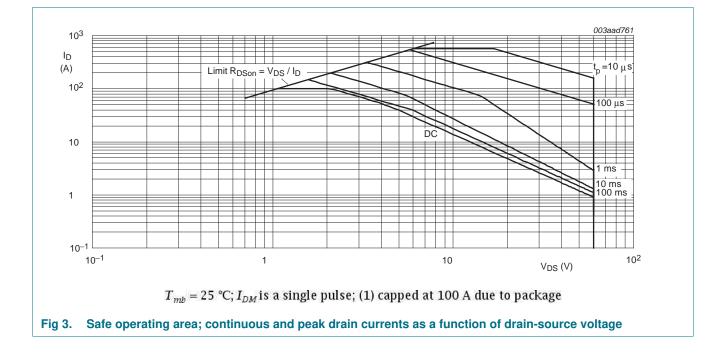


Fig 1. Continuous drain current as a function of mounting base temperature



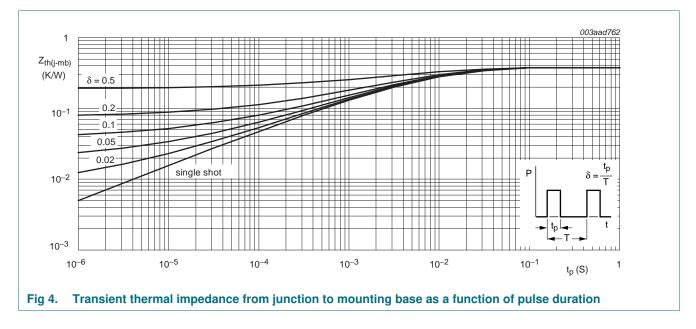


PSMN4R6-60BS



Thermal characteristics 6.

Table 6.	I hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W



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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	54	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	60	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V _{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS}=60~V;~V_{GS}=0~V;~T_{j}=25~^{\circ}C$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μΑ
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	8.6	10.1	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13	-	5.98	7	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	3.74	4.4	mΩ
R _G	gate resistance	f = 1 MHz	-	0.79	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	63	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	70.8	-	nC
Q _{GS}	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	19.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	13.5	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate-source charge		-	6	-	nC
Q _{GD}	gate-drain charge		-	14.8	-	nC
$V_{\text{GS}(\text{pl})}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4426	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	567	-	pF
C _{rss}	reverse transfer capacitance		-	293	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	58	-	ns
t _f	fall time		-	22	-	ns

Symbol

PSMN4R6-60BS

Тур

Unit

Max

N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

Min

ource-o	drain diode						
SD	source-drain voltage	I _S = 25 A; V _{GS} = 0 \ see <u>Figure 17</u>	/; T _j = 25 °C;	-	0.81	1.1	V
r	reverse recovery time	I _S = 25 A; dI _S /dt = -		-	45	-	ns
) _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 30$) V	-	64	-	nC
10	0	003aad763	100		(003aad769	
I _D (A)	15 6 5.5 5		9fs (S)				
8	0		80				
6	0		60				
		4.5					
4	0		40				
2		s (V) = 4	20				
			o 🖾 🖾				_
	0 0.5 1 1.	5 VDS (V) 2	0 20	40	60 80) 100 In (A)	0
	0 0.5 1 1.	⁵ V _{DS} (V) ²	0 20) _{ID} (A) ¹⁰⁰	0
	$T_j = 25 ^{\circ}C$	⁵ V _{DS} (V) ²	0 20	40 = 25 °C; V _L) 100 I _D (A)	D
Fig 5.	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain	current as a Fig	0 20 <i>T_j</i> : 6. Forward tra	= 25 °C; V_E	$\sigma_{S}=10~{ m V}$ ance as a		
Fig 5.	0 0.5 1 1. $T_j = 25 ^{\circ}C$	current as a Fig age; typical values	0 20 T_{j} :	= 25 °C; V_E	_{os} = 10 V ance as a alues	ı functio	
Fig 5. 10	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig	0 20 <i>T_j</i> : 6. Forward tra	= 25 °C; V_E	_{os} = 10 V ance as a alues		
Fig 5. 10 I _D	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig age; typical values	0 20 <i>T_j</i> : 6. Forward train drain current 8000 C	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764	
Fig 5. 10	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig age; typical values	0 20 T _j = 6. Forward train drain current 8000 C (pF)	= 25 °C; V_E	_{os} = 10 V ance as a alues	ı functio	
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Fig 5. 10 (A) 8	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig age; typical values	0 20 T _j = 6. Forward train drain current 8000 C (pF)	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
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Fig 5. 10 (A) 8	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig age; typical values	0 20 T _j = 6. Forward train drain current 8000 C (pF)	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
Fig 5. 10 (A) 8	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta	current as a Fig age; typical values	0 20 <i>T_j</i> = 6. Forward train drain current 8000 C (pF) 6000	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
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Fig 5. 10 (A) 8 6	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	current as a Fig age; typical values	0 20 <i>T_j</i> = 6. Forward train drain current 8000 C (pF) 6000	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
Fig 5. 10 (A) 8 6	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	Current as a age; typical values	0 20 <i>T_j</i> = 6. Forward train drain current 8000 C (pF) 6000 4000	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
Fig 5. 10 (A) 8 4 2	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta 0 0 1 1 1. 0 0 1 0 1. 0 0 0 1. 0 0 0 0 0 0. 0 0 0. 0 0 0 0. 0 0 0.	Current as a age; typical values	0 20 <i>T_j</i> = 6. Forward tran drain curren 8000 C (pF) 6000 4000 2000	= 25 °C; V_E	_{os} = 10 V ance as a alues	003aad764 C _{iss}	
Fig 5. 10 (A) 8 4 2	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	Current as a age; typical values	0 20 <i>T_j</i> = 6. Forward train drain current 8000 C (pF) 6000 4000	= 25 °C; V_E	estimate as a second se	003aad764 C _{iss}	on of
Fig 5. 10 (A) 8 4 2	0 0.5 1 1. $T_j = 25 ^{\circ}C$ Output characteristics: drain function of drain-source volta 0 T_j = 175 ^{\circ}C	Current as a age; typical values	0 20 <i>T_j</i> : 6. Forward train drain current 8000 C (pF) 6000 4000 2000 0 0	= 25 °C; V _E nsconduct nt; typical v	estimates a second seco	C _{rss}	on of

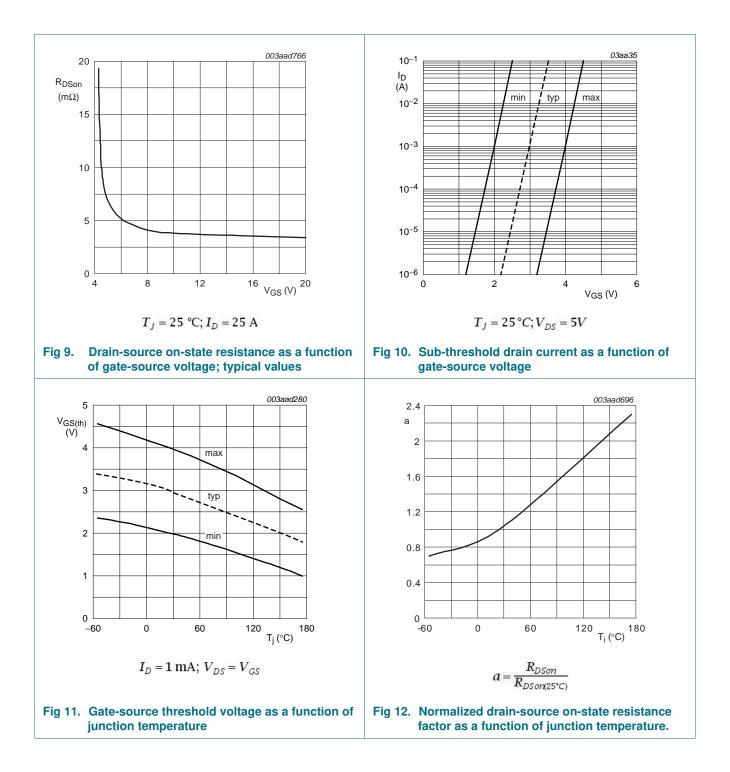
Conditions

Table 7. Characteristics ... continued Parameter

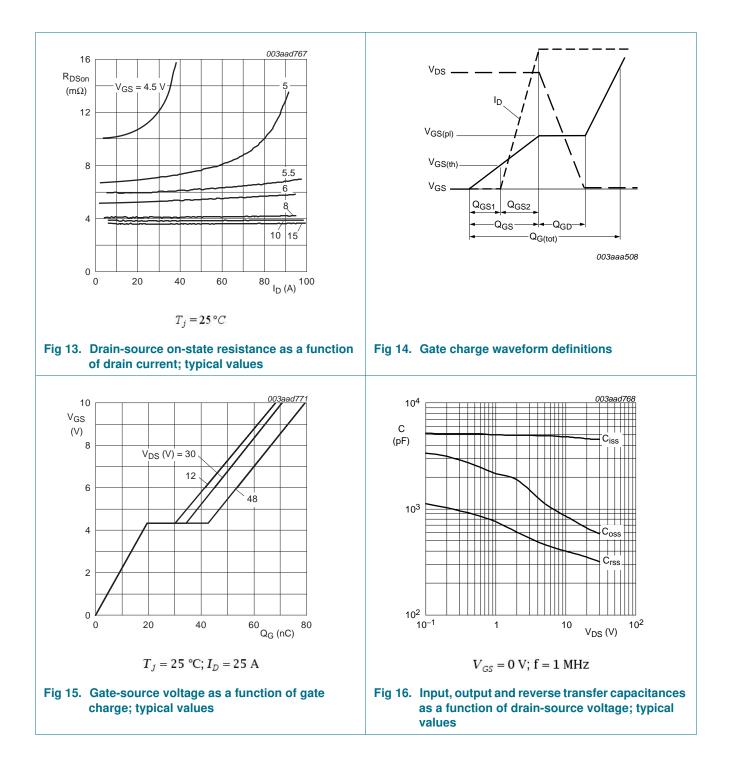
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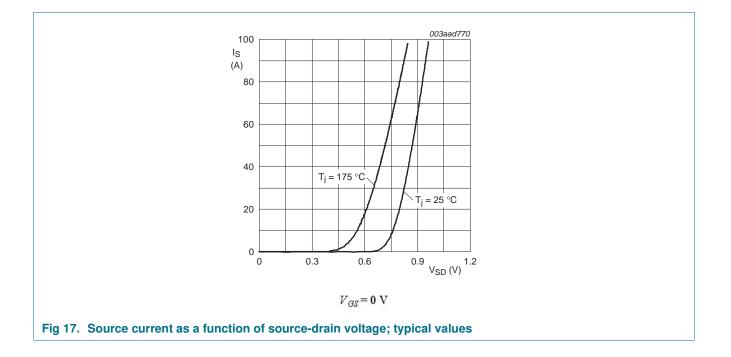
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N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK

8. Package outline

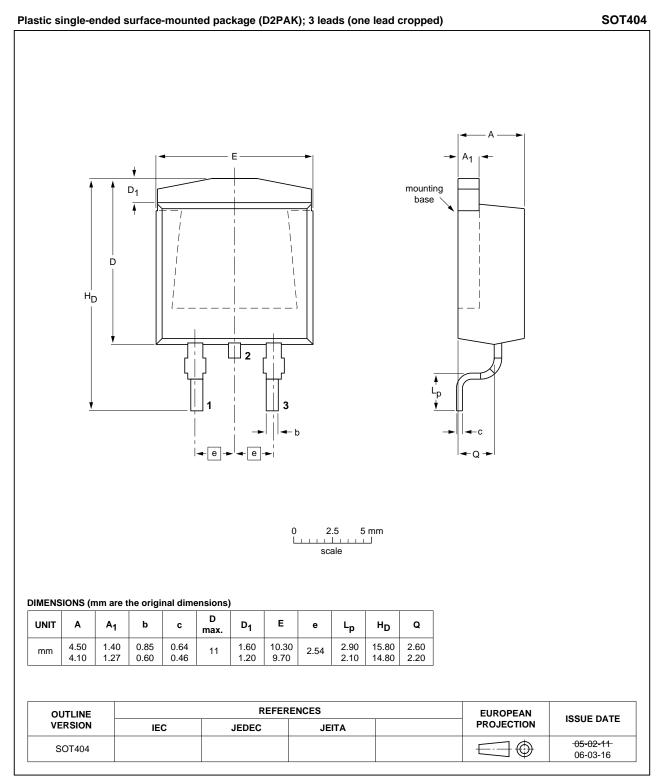


Fig 18. Package outline SOT404 (D2PAK)

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PSMN4R6-60BS

9. Revision history

Table 8. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R6-60BS v.1	20120322	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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